### 2.5V Drive Pch+SBD MOSFET

V <sub>DSS</sub>	-20V
R <sub>DS(on)</sub> (Max.)	200mΩ
I <sub>D</sub>	±1.5A
P <sub>D</sub>	1.25W

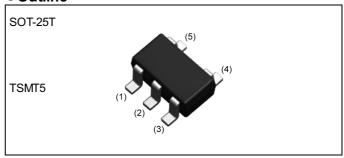
#### Features

- The QS5U26 combines Pch MOSFET with a Schottky barrier diode in a single TSMT5 package.
- 2) Low on-state resistance with fast swicthing
- 3) Low voltage drive (2.5V drive).
- 4) Built-in Low V<sub>F</sub> schottky barrier diode.
- 5) Pb-free lead plating; RoHS compliant.

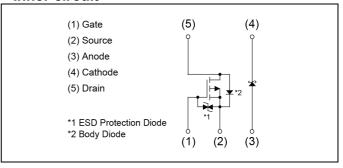
## Application

Load switch, DC/ DC conversion

## Outline



### •Inner circuit



Packaging specifications

	Packing	Embossed Tape
	Reel size (mm)	180
Туре	Tape width (mm)	8
	Quantity (pcs)	3000
	Taping code	TR
	Marking	U26

## ● **Absolute maximum ratings** (T<sub>a</sub> = 25°C ,unless otherwise specified)

#### <MOSFET>

Parameter	Symbol	Value	Unit
Drain - Source voltage	V <sub>DSS</sub>	-20	V
Gate - Source voltage	V <sub>GSS</sub>	±12	V
Continuous drain current	I <sub>D</sub>	±1.5	А
Pulsed drain current	I <sub>DP</sub> *1	±6.0	А
Continuous source current (body diode)	I <sub>S</sub>	-0.75	А
Pulsed source current (body diode)	I <sub>SP</sub> *1	-3.0	А
Power dissipation	P <sub>D</sub> *3	0.9	W/element
Junction temperature	T <sub>j</sub>	150	°C

# ● Absolute maximum ratings (T<sub>a</sub> = 25°C)

## <Di>

Parameter	Symbol	Value	Unit
Repetitive peak reverse voltage	$V_{RM}$	30	V
Reverse voltage	V <sub>R</sub>	20	V
Forward current	I <sub>F</sub>	0.5	Α
Forward current surge peak	I <sub>FSM</sub> *2	2.0	Α
Power dissipation	P <sub>D</sub> *3	0.7	W/element
Junction temperature	T <sub>j</sub>	150	°C

## <MOSFET + Di>

Parameter	Symbol	Value	Unit
Power dissipation	P <sub>D</sub> *3	1.25	W/total
Operating junction and storage temperature range	T <sub>stg</sub>	-55 to +150	°C

# ●Electrical characteristics (T<sub>a</sub> = 25°C)

## <MOSFET>

Darameter	Sumb of	Conditions	Values			Unit
Parameter	Symbol	Symbol Conditions		Тур.	Max.	Uniil
Gate - Source leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 12V, V_{DS} = 0V$	-	-	±10	μΑ
Drain - Source breakdown voltage	V <sub>(BR)DSS</sub>	$V_{(BR)DSS}$ $V_{GS} = 0V, I_D = -1mA$		-	-	V
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V	-	-	-1	μA
Gate threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = -10V, I_{D} = -1mA$	-0.7	-	-2.0	V
		$V_{GS} = -4.5V, I_D = -1.5A$	-	160	200	
Static drain - source on - state resistance	R <sub>DS(on)</sub> *4	$V_{GS} = -4V, I_D = -1.5A$	-	180	240	mΩ
		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -0.75A	-	260	340	
Forward Transfer Admittance	Y <sub>fs</sub>  *4	V <sub>DS</sub> = -10V, I <sub>D</sub> = -0.75A	1.0	-	-	S

# ●Electrical characteristics (T<sub>a</sub> = 25°C)

## <MOSFET>

Parameter	Symbol	Conditions	Values			Unit
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Offit
Input capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V	-	325	-	
Output capacitance	C <sub>oss</sub>	V <sub>DS</sub> = -10V	-	60	-	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1MHz	-	40	-	
Turn - on delay time	t <sub>d(on)</sub> *4	$V_{DD} \simeq$ -15V, $V_{GS} =$ -4.5V	-	10	-	
Rise time	t <sub>r</sub> *4	I <sub>D</sub> = -0.75A	-	10	-	no
Turn - off delay time	t <sub>d(off)</sub> *4	$R_L = 20\Omega$	-	35	-	ns
Fall time	t <sub>f</sub> *4	$R_G = 10\Omega$	-	10	-	

# ● Gate charge characteristics (T<sub>a</sub> = 25°C)

## <MOSFET>

Parameter	Symbol	Conditions	Values			Unit
raianetei	Symbol	Conditions	Min.	Тур.	Max.	Offic
Total gate charge	$Q_g^{*4}$		-	4.2	-	
Gate - Source charge	Q <sub>gs</sub> *4	$V_{DD} \simeq -15V, I_{D} = -1.5A$ $V_{GS} = -4.5V$	-	1.0	-	nC
Gate - Drain charge	Q <sub>gd</sub> *4	765 1.07	-	1.1	-	

## ● Body diode electrical characteristics (Source-Drain) (T<sub>a</sub> = 25°C)

## <MOSFET>

Parameter	Symbol	Conditions	Values			Linit
	Symbol	Conditions	Min.	Тур.	Max.	Unit
Forward voltage	$V_{SD}^{*4}$	$V_{GS} = 0V, I_{S} = -0.75A$	-	-	-1.2	V

3/10

# ● Electrical characteristics (T<sub>a</sub> = 25°C)

## <Di>

Davamatan	Cy made al	Conditions	Values			1.1-:4
Parameter	Symbol	Symbol Conditions		Тур.	Max.	Unit
Forward voltage	$V_{F}$	I <sub>F</sub> = 0.1A	-	-	0.36	V
		I <sub>F</sub> = 0.5A	-	-	0.47	V
Reverse current	I <sub>R</sub>	V <sub>R</sub> = 20V	-	-	100	μA

<sup>\*1</sup> Pw ≤ 10µs, Duty cycle ≤ 1%

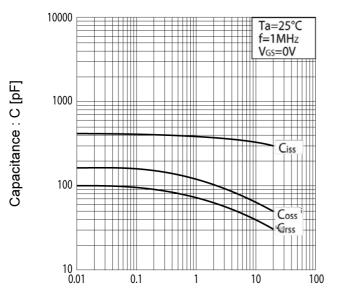
<sup>\*2 60</sup>Hz-1 cycle

<sup>\*3</sup> Mounted on a ceramic board

<sup>\*4</sup> Pulsed

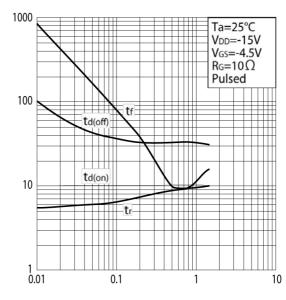
#### • Electrical characteristic curves < MOSFET>

Fig.1 Typical Capacitance vs. Drain - Source Voltage



Drain - Source Voltage :  $-V_{DS}[V]$ 

Fig.2 Switching Characteristics



Drain Current: -ID [A]

Fig.3 Typical Transfer Characteristics

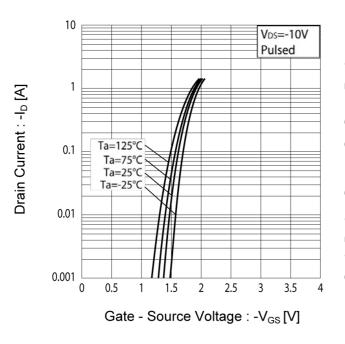
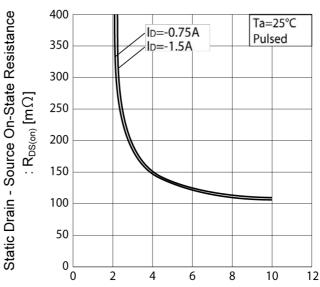


Fig.4 Static Drain - Source On - State Resistance vs. Gate Source Voltage

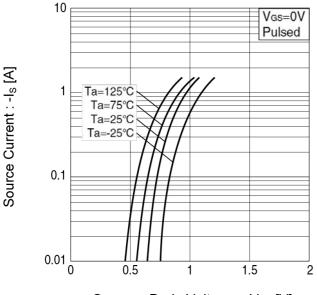


Gate - Source Voltage : -V<sub>GS</sub> [V]

Switching Time : t [ns]

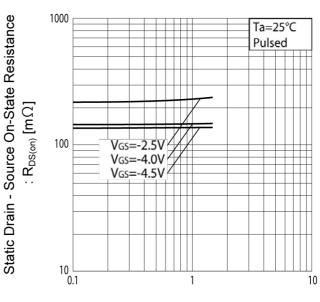
### ● Electrical characteristic curves < MOSFET>

Fig.5 Source Current vs. Source Drain Voltage



Source - Drain Voltage : -V<sub>SD</sub> [V]

Fig.6 Static Drain - Source On - State Resistance vs. Drain Current (I)

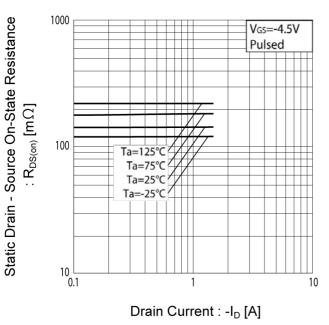


Drain Current: -ID [A]

Fig.8 Static Drain - Source On - State

Resistance vs. Drain Current (III)

Fig.7 Static Drain - Source On - State Resistance vs. Drain Current (II)



Static Drain - Source On-State Resistance :  $R_{DS(on)} \, [m\Omega]$ 

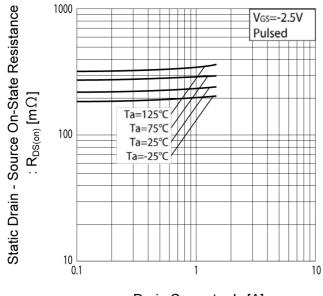
1000 VGS=-4V Pulsed

100 Ta=125°C Ta=75°C Ta=25°C Ta=-25°C Ta=-25°C

Drain Current: -I<sub>D</sub> [A]

## ● Electrical characteristic curves < MOSFET>

Fig.9 Static Drain - Source On - State Resistance vs. Drain Current (IV)



Drain Current : -I<sub>D</sub> [A]

## ● Electrical characteristic curves < Diode >

Fig.11 Forward Current vs. Forward Voltage

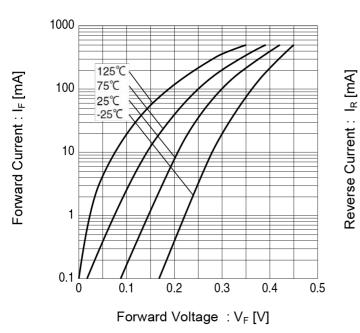
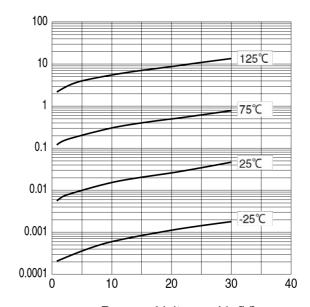


Fig.12 Reverse Current vs. Reverse Voltage



Reverse Voltage: V<sub>R</sub> [V]

#### Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

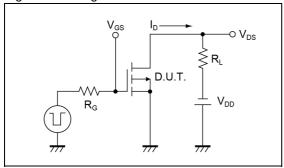


Fig.2-1 Gate Charge Measurement Circuit

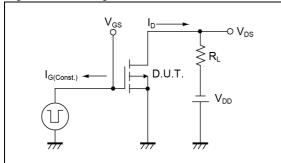


Fig.1-2 Switching Waveforms

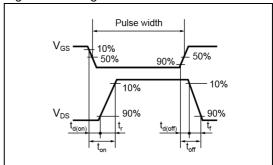
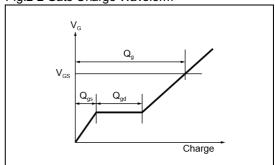


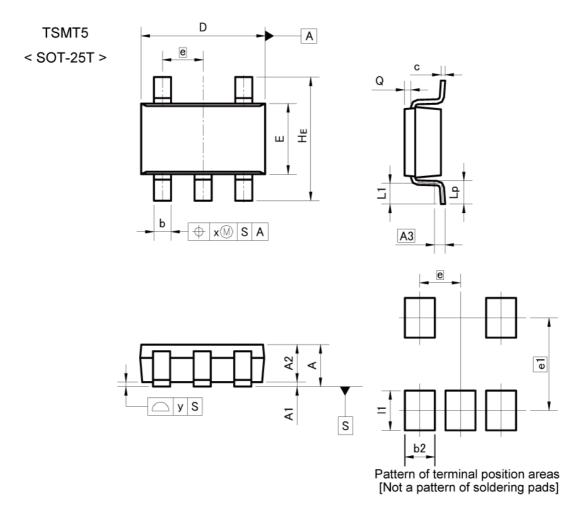
Fig.2-2 Gate Charge Waveform



#### Notice

- SBD has a large reverse leak current compared to other type of diode. Therefore, it would raise a junction temperature, and increase a reverse power loss. Further rise of inside temperature would cause a thermal runaway. This built-in SBD has low V<sub>F</sub> characteristics and therefore, higher leak current. Please consider enough the surrounding temperature, generating heat of MOSFET and the reverse current.
- 2. This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

## Dimensions



DIM	MILIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8 <u>22</u>	1.00	=	0.039
A1	0.00	0.10	0.000	0.004
A2	0.75	0.95	0.030	0.037
A3	0.	25	0.0	10
b	0.35	0.50	0.014	0.020
С	0.10	0.26	0.004	0.010
D	2.80	3.00	0.110	0.118
E	1.50	1.80	0.059	0.071
е	0.	95	0.037	
HE	2.60	3.00	0.102	0.118
L1	0.30	0.60	0.012	0.024
Lp	0.40	0.70	0.016	0.028
Q	0.05	0.25	0.002	0.010
х	2.77	0.20	==	0.008
У	<del>(-</del>	0.10	#	0.004

MILIMETERS INCHES DIM MIN MIN MAX MAX b2 0.70 0.028 2.10 0.083 e1 11 0.90 0.035

Dimension in mm/inches



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(Note1) Medical Equipment Classification of the Specific Applications

JÁPAN	USA	EU	CHINA
CLASSⅢ	CL ACCIII	CLASS II b	CL ACCIII
CLASSIV	CLASSⅢ	CLASSⅢ	CLASSⅢ

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  - [b] Installation of redundant circuits to reduce the impact of single or multiple circuit failure
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  - [a] Use of our Products in any types of liquid, including water, oils, chemicals, and organic solvents
  - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
  - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl<sub>2</sub>, H<sub>2</sub>S, NH<sub>3</sub>, SO<sub>2</sub>, and NO<sub>2</sub>
  - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
  - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
  - [f] Sealing or coating our Products with resin or other coating materials
  - [g] Use of our Products without cleaning residue of flux (Exclude cases where no-clean type fluxes is used. However, recommend sufficiently about the residue.); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
  - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse, is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

#### Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

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#### **Precaution for Electrostatic**

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

#### **Precaution for Storage / Transportation**

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
  - [a] the Products are exposed to sea winds or corrosive gases, including Cl<sub>2</sub>, H<sub>2</sub>S, NH<sub>3</sub>, SO<sub>2</sub>, and NO<sub>2</sub>
  - [b] the temperature or humidity exceeds those recommended by ROHM
  - [c] the Products are exposed to direct sunshine or condensation
  - [d] the Products are exposed to high Electrostatic
- Even under ROHM recommended storage condition, solderability of products out of recommended storage time period
  may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is
  exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

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